

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office JUN 04 2004 LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Attorney Docket Number: 308,757IP2		Serial No.: 10/045,542	
				Applicants: Das et al.			
				Filing Date: October 26, 2001		Group: 1762	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	1	Williams et al., "Passivation of the 4-H SiC/SiO ₂ Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.					
	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.					

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				Applicants: Das et al.			
				Filing Date: October 26, 2001		Group: 1762	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	5,479,316	12/26/95	Smrtic et al.	361	322	
	2	5,739,564	04/14/98	Kosa et al.	257	298	
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	
	4	6,239,463	05/29/01	Williams et al.	257	328	
	5	6,316,791	11/13/01	Schorner et al.	257	77	
	6	6,593,620	07/15/03	Hshieh et al.	257	335	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
	7	WO 98/02924	01/22/98	PCT			
	8	WO 00/13236	03/09/00	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	9	Dimitrijevic et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.					
	10	De Mao et al., "Thermal Oxidation of SiC in N ₂ O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.					
	11	Ryu et al., Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.					

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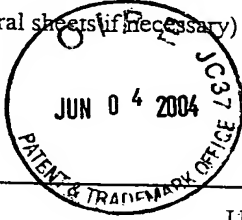
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	1	5,587,870	12/24/96	Anderson et al.	361	313	
	2	5,877,045	3/2/99	Kapoor	438	151	

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		Document Number	Date	Country	Class	Subclass	Translation Yes No
	3	WO99/63591	12/9/99	PCT			

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	4	Mutin, P. Herbert, "Control of the Composition and Structure of Silicon Oxycarbide and Oxynitride Glasses Derived from Polysiloxane Precursors," <i>Journal of Sol-Gel Science and Technology</i> . Vol. 14 (1999) pp. 27-38.
	5	del Prado et al. "Full Composition Range Silicon Oxynitride Films Deposited by ECR-PECVD at Room Temperatures," <i>Thin Solid Films</i> . Vol. 343-344 (1999) p. 437-440.
	6	Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," <i>IEEE Transactions on Electron Devices</i> . Vol. 47, No. 2, February 2000.
	7	International Search Report for PCT/US02/09393 dated 10/15/03.

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